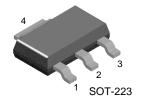


NZT660/NZT660A

PNP Low Saturation Transistor

• These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	NZT660	NZT660A	Units
V _{CEO}	Collector-Emitter Voltage	60	60	V
V_{CBO}	Collector-Base Voltage	80	60	V
V _{EBO}	Emitter-Base Voltage	5	5	V
I _C	Collector Current - Continuous	3	3	Α
T_J , T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +150	- 55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150°C.

 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics	·	•	•	•	
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA	60			V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100μA NZT660	80			V
		NZT660A	60			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 100 \mu A$	5			V
I _{CBO}	Collector-Base Cutoff Current	V _{CB} = 30V			100	nA
		$V_{CB} = 30V, T_A = 100^{\circ}C$			10	μΑ
I _{EBO}	Emitter-Base Cutoff Current	$V_{EB} = 4V$			100	nA
On Charac	teristics *		_	_	_	
h _{FE}	DC Current Gain	I _C = 100mA, V _{CE} = 2V	70			
		$I_C = 500$ mA, $V_{CE} = 2V$ NZT660	100		300	
		NZT660A	250		550	
		$I_C = 1A$, $V_{CE} = 2V$	80			
		$I_C = 3A$, $V_{CE} = 2V$	25			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 100mA$			300	mV
		$I_C = 3A, I_B = 300mA$ NZT660			550	mV
		NZT660A			500	mV
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 1A, I _B = 100mA			1.25	V
V _{BE} (on)	Base-Emitter On Voltage	I _C = 1A, V _{CE} = 2V			1	V
Small Sign	nal Characteristics					
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$			45	pF
f⊤	Transition Frequency	$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$				MHz

Thermal Characteristics T _A =25°C unless otherwise noted			
Symbol	Devemeter	Max.	Units
	Parameter	NZT660/NZT660A	Units
P _D	Total Device Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	°C/W

Typical Characteristics

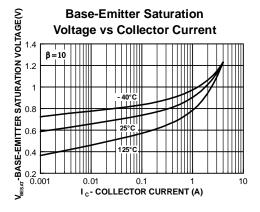


Figure 1. Base-Emitter Saturation Voltage vs Collector Current

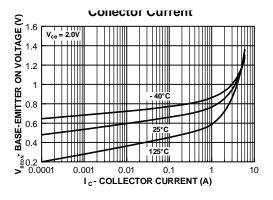


Figure 2. Base-Emitter On Voltag vs Collector Current

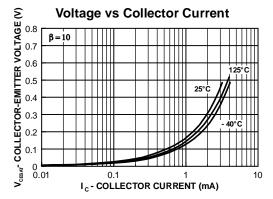


Figure 3. Collector-Emitter Saturation Voltage vs Collector Current

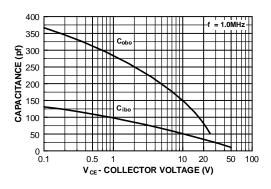


Figure 4. Input/Output Capacitance vs Reverse Bias Voltage

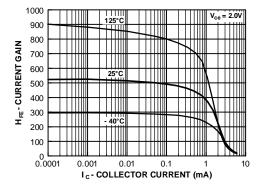
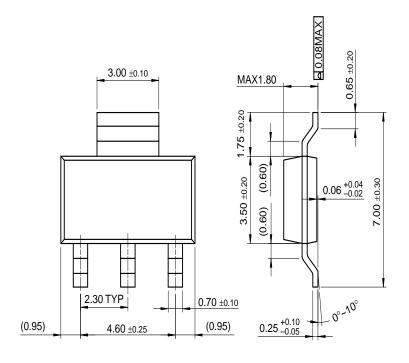
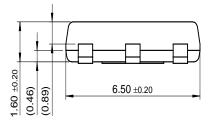


Figure 5. Current Gain vs Collector Current

Package Dimensions

SOT-223





Dimensions in Millimeters

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E ² CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I ² C TM	OCX^{TM}	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET [®]
The Power Franchise™		OPTOLOGIC [®]	SILENT SWITCHER®	VCX^{TM}
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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